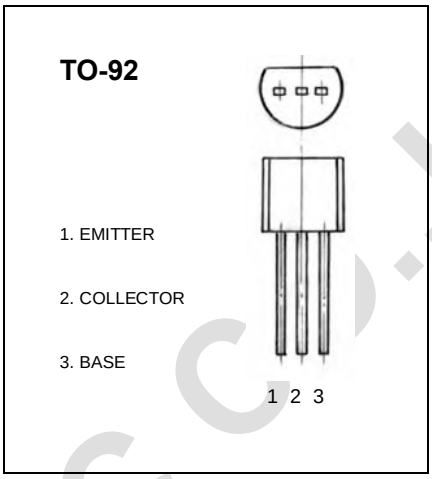
D965 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 0.75 W (Tamb=25℃)

Collector current

$I_{CM:}$ 5 A

Collector-base voltage

$V_{(BR)CBO}$: 42 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=1mA, I_E=0	42			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 1mA, I_B=0	22			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 10μA, I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}= 30V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 6V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= 2V, I_C= 0.15 mA	150			
	$h_{FE(2)}$	V_{CE}= 2V, I_C = 500 mA	340		950	
	$h_{FE(3)}$	V_{CE}=2V, I_C = 2000 mA	150			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=3000mA, I_B=100 mA			0.35	V

CLASSIFICATION OF $h_{FE(2)}$

Rank	R	T
Range	340-600	560-950

WEJ ELECTRONIC CO.,LTD